



DMP2123L

#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

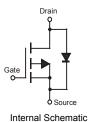
#### **Features**

- Low R<sub>DS(ON)</sub>
  - 72 mΩ @V<sub>GS</sub> = -4.5V
  - 108 m $\Omega$  @V<sub>GS</sub> = -2.7V
  - 123 mΩ @V<sub>GS</sub> = -2.5V
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

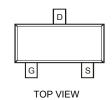
### **Mechanical Data**

- Case: SOT23
- Case Material Molded Plastic, "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
   Solderable per MIL-STD-202, Method 208 3
- Terminal Connections: See Diagram Below
- Weight: 0.008 grams (approximate)





SOT23



internal Sch

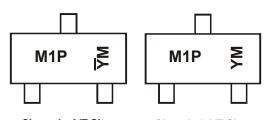
# Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2123L-7	SOT-23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

## **Marking Information**



M1P = Product Type Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)

 $\overline{Y}$ M = Date Code Marking for SAT (Shanghai Assembly/ Test site)  $\overline{Y}$ M = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or  $\overline{Y}$  = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Chengdu A/T Site Shanghai A/T Site

#### Date Code Key

Year	2007	2008	2009	2010	201	1 20	)12	2013	2014	2015	2016	2017
Code	U	V	W	X	Y		Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	-20	V
Gate-Source Voltage		$V_{GSS}$	±12	V
Drain Current (Note 5) Continuous	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	l <sub>D</sub>	-3.0 -2.4	А
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-15	Α
Body-Diode Continuous Current (Note 5)		Is	2.0	A

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	1.4	W
Thermal Resistance, Junction to Ambient (Note 5); Steady-State	$R_{ heta JA}$	90	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 5. Device mounted on 1"x1", FR-4 PC board with 2 oz. Copper and test pulse width t  $\leq$ 10s. 6. Repetitive Rating, pulse width limited by junction temperature.

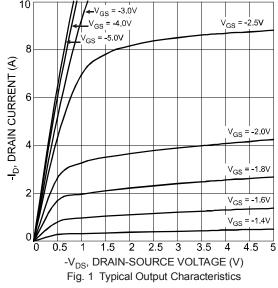
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

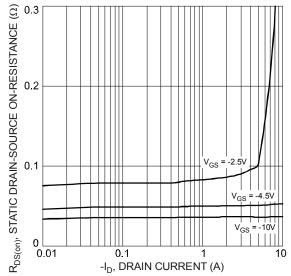
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
STATIC PARAMETERS								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20		_	V	$I_D = -250 \mu A, V_{GS} = 0 V$		
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$		
Gate-Body Leakage Current	I <sub>GSS</sub>	_	_	±100	nA	$V_{DS} = 0V, V_{GS} = \pm 12V$		
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.6		-1.25	>	$V_{DS} = V_{GS}, I_D = -250 \mu A$		
On State Drain Current (Note 7)	I <sub>D (ON)</sub>	-15		_	Α	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -5V		
			51	72		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.5A		
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(ON)</sub>	_	87	108	$m\Omega$	$V_{GS} = -2.7V$ , $I_D = -3.0A$		
			99	123		$V_{GS} = -2.5V, I_D = -2.6A$		
Forward Transconductance (Note 7)	<b>g</b> FS	_	7.3		S	$V_{DS} = -10V, I_D = -3.0A$		
Diode Forward Voltage (Note 5)	$V_{SD}$	_	0.79	-1.26	٧	$I_S = -1.7A$ , $V_{GS} = 0V$		
Maximum Body-Diode Continuous Current (Note 5)	Is	_		1.7	Α	_		
DYNAMIC PARAMETERS (Note 8)								
Total Gate Charge	$Q_g$	_	7.3		nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_D = -3.0A$		
Gate-Source Charge	Qgs	_	2.0		nC	$V_{GS} = -4.5V$ , $V_{DS} = -10V$ , $I_D = -3.0A$		
Gate-Drain Charge	$Q_{gd}$	_	1.9	_	nC	$V_{GS}$ = -4.5V, $V_{DS}$ = -10V, $I_{D}$ = -3.0A		
Turn-On Delay Time	t <sub>D(on)</sub>	_	12	_	ns			
Turn-On Rise Time Turn-Off Delay Time		_	20	_	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$		
		_	38	_	ns	$R_L = 10\Omega$ , $R_G = 6\Omega$		
Turn-Off Fall Time	t <sub>f</sub>	_	41	_	ns	]		
Input Capacitance Output Capacitance		_	443	_	pF	401/1/		
		_	128	_	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	101		pF	- 1.UIVINZ		

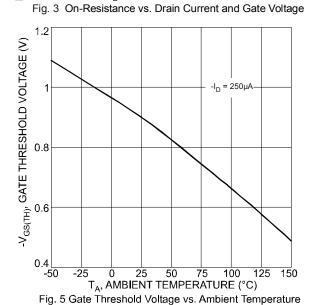
Notes: 7. Test pulse width  $t = 300 \mu s$ .

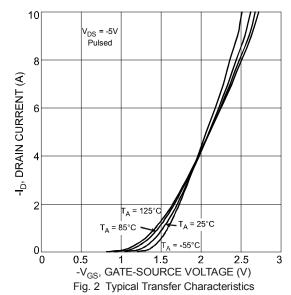
8. Guaranteed by design. Not subject to production testing.

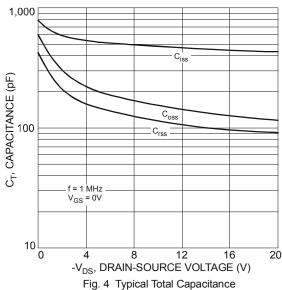












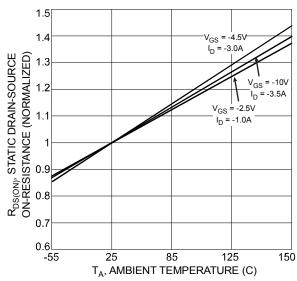


Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



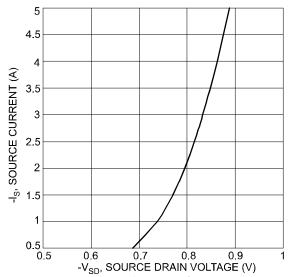
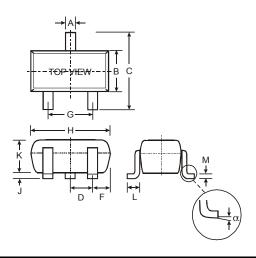


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

## **Package Outline Dimensions**

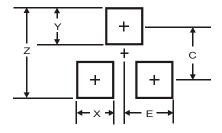
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
M	0.085	0.180			
α	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	2.9
Х	8.0
Y	0.9
С	2.0
E	1.35



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